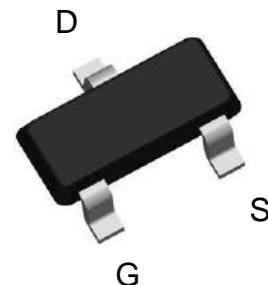


## N-Channel Enhancement Mode Power MOSFET

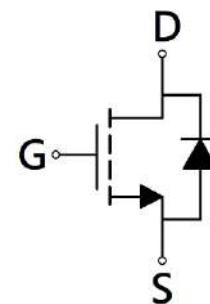
### Features:

- Low On Resistance
- Low Gate Charge
- Fast Switching Characteristic

SOT-23



BVDSS	20V
ID@VGS=4.5V, TA=25°C	4.3A
RDS(ON) typ. @ VGS=4.5V, ID=3.5A	30mΩ
RDS(ON) typ. @ VGS=2.5V, ID=3A	38mΩ
RDS(ON) typ. @ VGS=1.8V, ID=2A	45mΩ



G : Gate S : Source D : Drain

### Ordering Information

Device	Package	Shipping
KWA42N02	SOT-23 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel

### Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ )

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	
Continuous Drain Current @ $V_{GS}=4.5\text{V}$ , $T_A=25^\circ\text{C}$	$I_D$	4.3	A
Continuous Drain Current @ $V_{GS}=4.5\text{V}$ , $T_A=70^\circ\text{C}$		3.4	
Pulsed Drain Current	$I_{DM}$	17	A
Continuous Body Diode Forward Current @ $T_A=25^\circ\text{C}$	$I_S$	1	
Total Power Dissipation	$P_D$	1.4	W
$T_A=70^\circ\text{C}$		0.9	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150	°C

### Thermal Data

Parameter	Symbol	Steady State	Unit
Thermal Resistance, Junction-to-ambient	$R_{\theta JA}$	90	°C/W

Note:

- \*a. The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR -4 board with 2 oz. copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The power dissipation  $P_D$  is based on  $R_{\theta JA}$  and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- \*b. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}=150^\circ\text{C}$ . Ratings are based on low frequency and low duty cycles to keep initial  $T_J=25^\circ\text{C}$ .

### **Electrical Characteristics ( $T_A=25^\circ\text{C}$ , unless otherwise specified)**

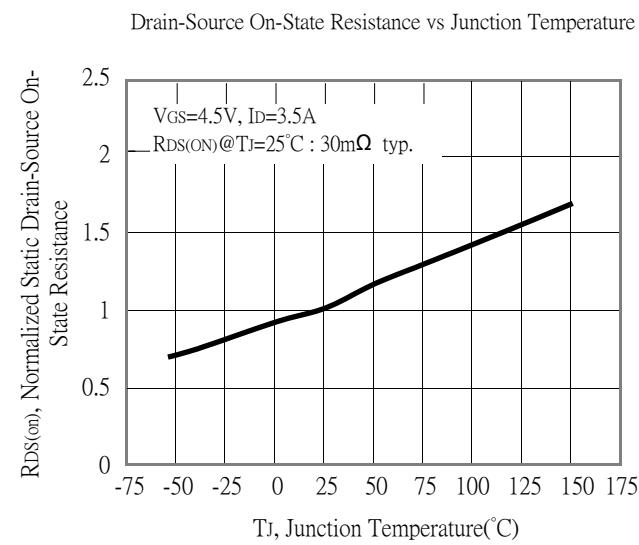
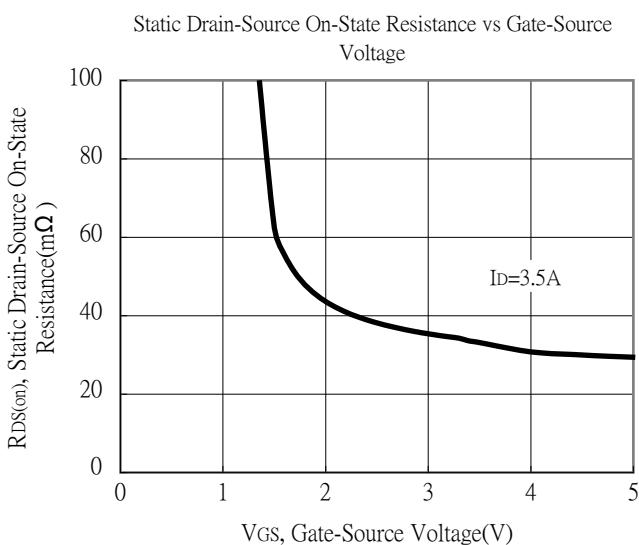
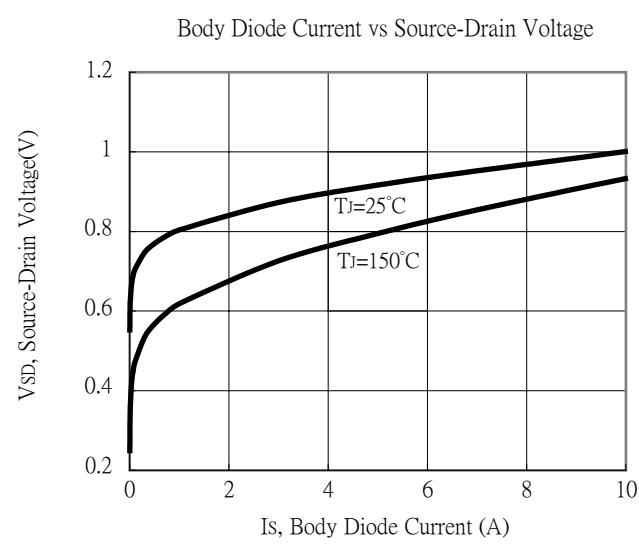
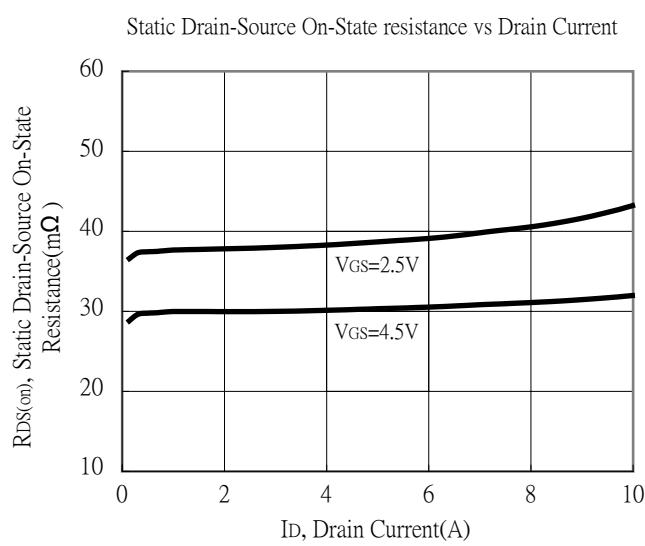
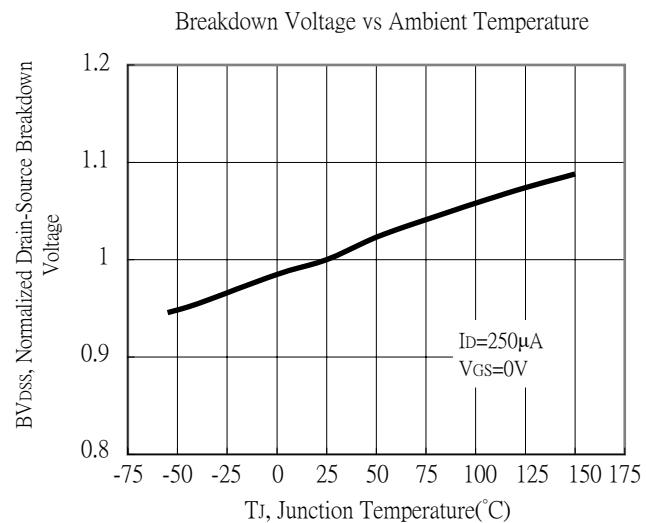
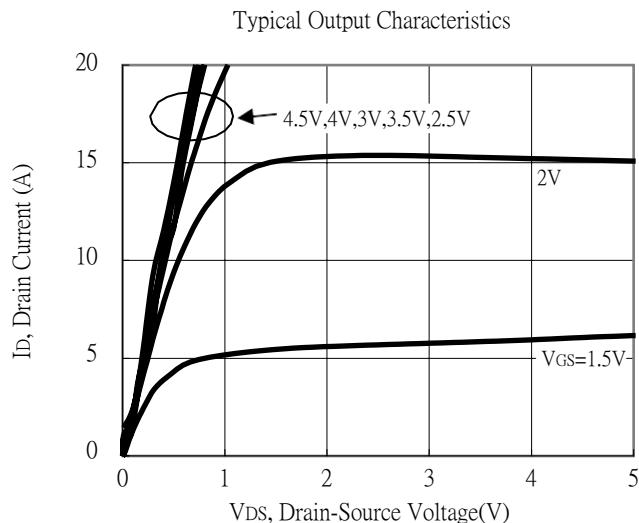
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
<b>Static</b>					
BV <sub>DSS</sub>	20	-	-	V	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA
V <sub>GS(th)</sub>	0.35	-	1		V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA
G <sub>FS</sub>	-	6.4	-	S	V <sub>DS</sub> =5V, I <sub>D</sub> =3A
I <sub>GSS</sub>	-	-	±100	nA	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V
I <sub>DSS</sub>	-	-	1	μA	V <sub>DS</sub> =16V, V <sub>GS</sub> =0V
R <sub>DSS(ON)</sub>	-	30	42	mΩ	V <sub>GS</sub> =4.5V, I <sub>D</sub> =3.5A
	-	38	60		V <sub>GS</sub> =2.5V, I <sub>D</sub> =3A
	-	45	90		V <sub>GS</sub> =1.8V, I <sub>D</sub> =2A
<b>Dynamic</b>					
C <sub>iss</sub>	-	290	-	pF	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHz
C <sub>oss</sub>	-	52	-		
C <sub>rss</sub>	-	48	-		
R <sub>g</sub>	-	1.5	-	Ω	f=1MHz
Q <sub>g</sub> *1, 2	-	5.1	-	nC	V <sub>DS</sub> =10V, I <sub>D</sub> =3.5A, V <sub>GS</sub> =4.5V
Q <sub>gs</sub> *1, 2	-	0.5	-		
Q <sub>gd</sub> *1, 2	-	1.5	-		
t <sub>d(ON)</sub> *1, 2	-	3.3	-	ns	V <sub>DS</sub> =10V, I <sub>D</sub> =3.5A, V <sub>GS</sub> =4.5V, R <sub>GS</sub> =6Ω
t <sub>r</sub> *1, 2	-	15	-		
t <sub>d(OFF)</sub> *1, 2	-	26	-		
t <sub>f</sub> *1, 2	-	7	-		
<b>Source-Drain Diode</b>					
V <sub>SD</sub> *1	-	0.83	1.2	V	I <sub>S</sub> =1.6A, V <sub>GS</sub> =0V
trr	-	5.3	-	ns	I <sub>F</sub> =1.6A, dI <sub>F</sub> /dt=100A/μs
Qrr	-	1.6	-	nC	

Note:

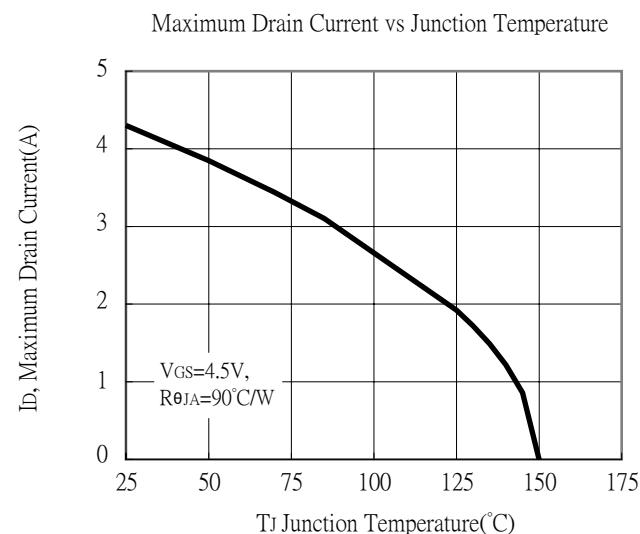
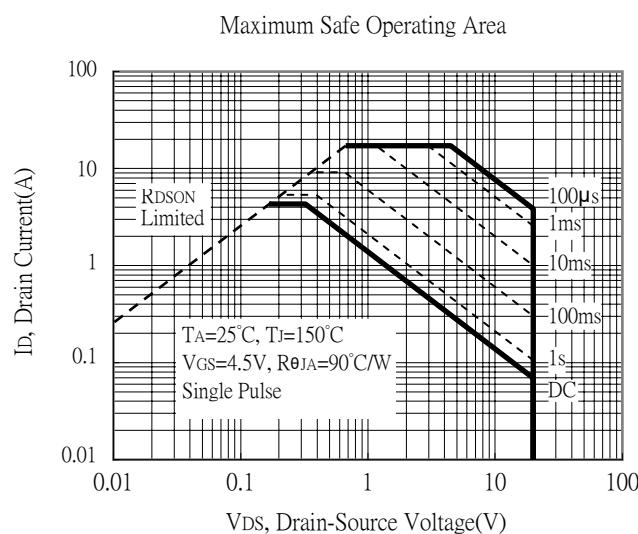
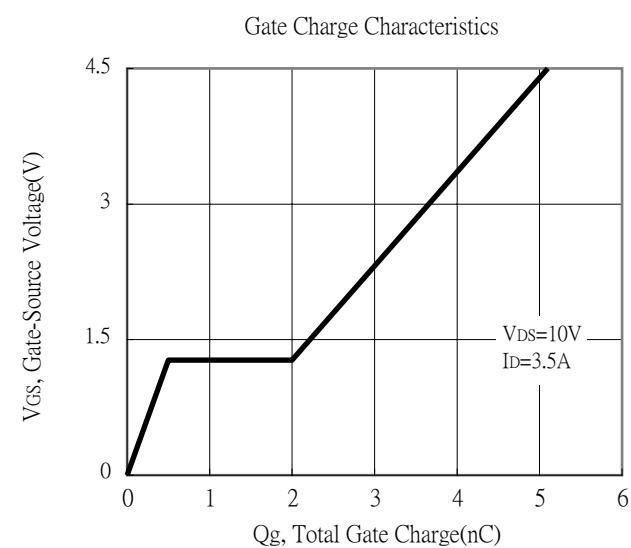
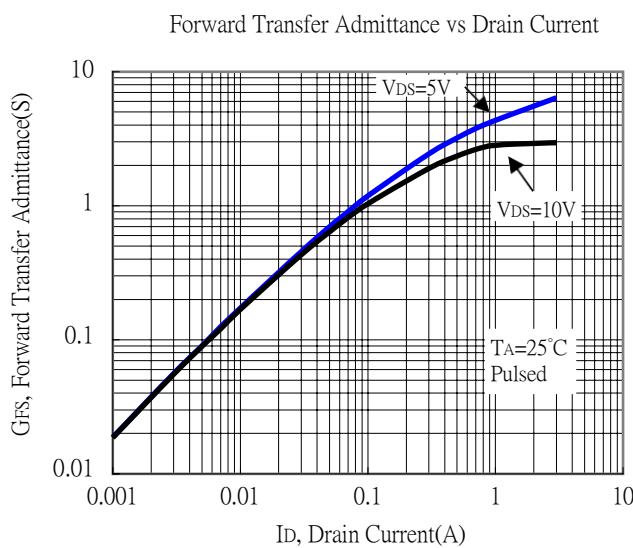
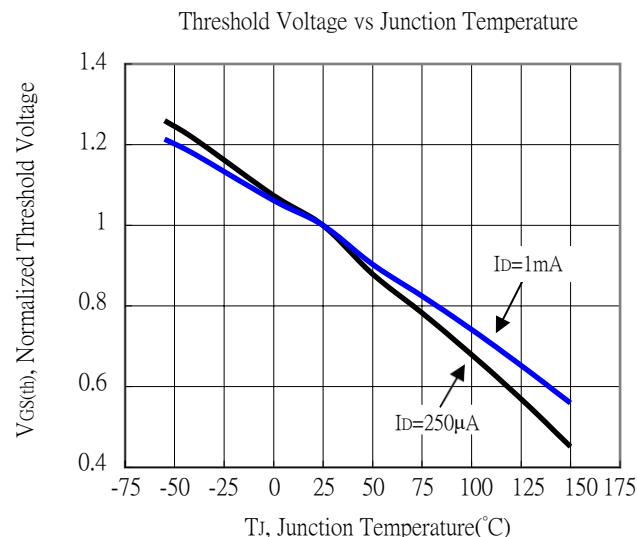
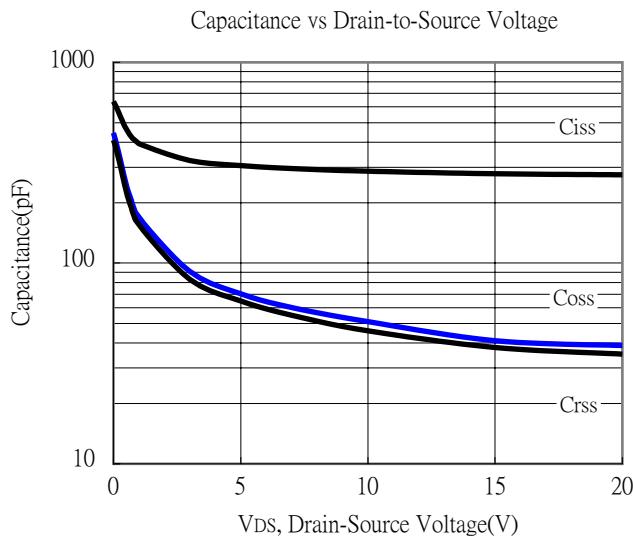
\*1. Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

\*2. Independent of operating temperature

## Typical Characteristics

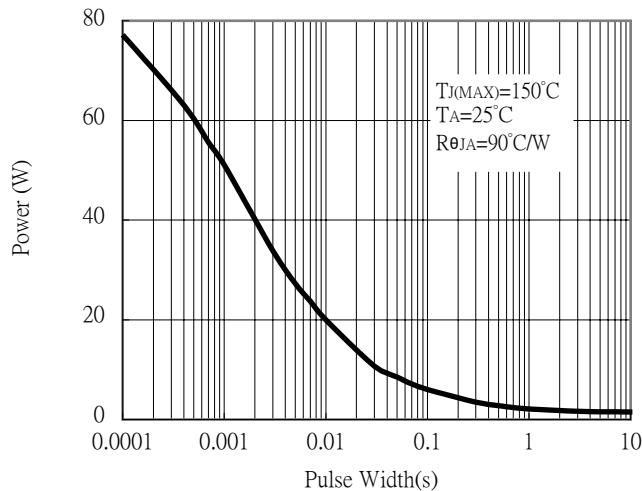


## Typical Characteristics (Cont.)

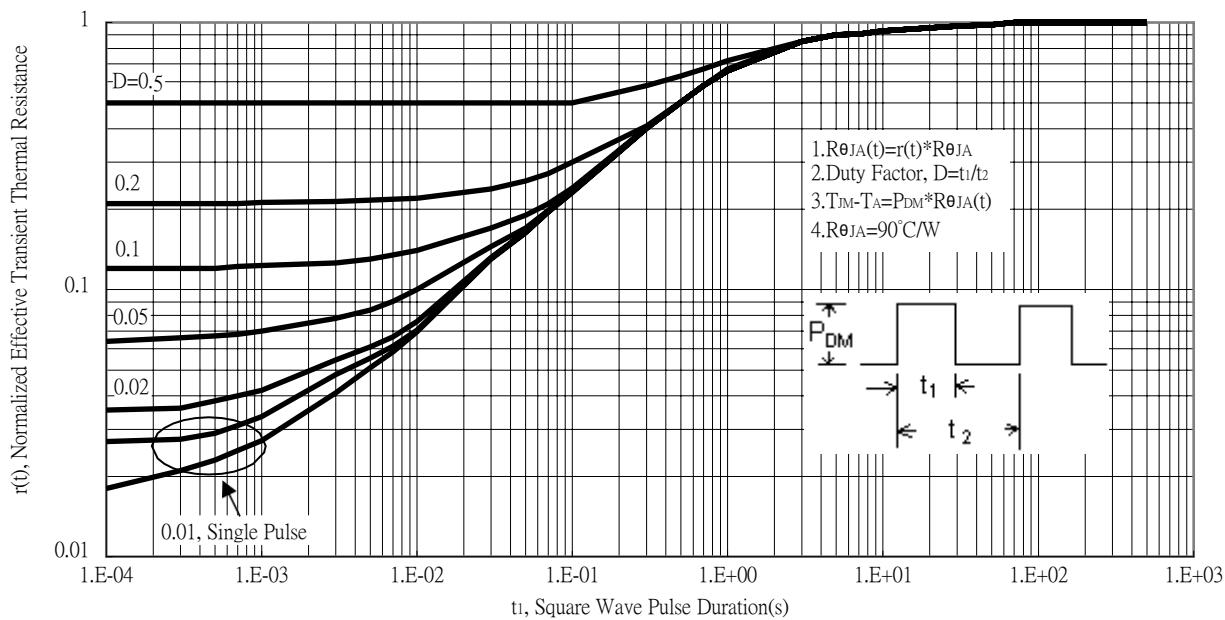


## Typical Characteristics (Cont.)

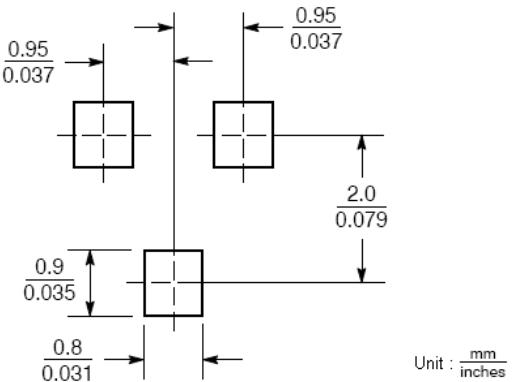
Single Pulse Power Rating, Junction to Ambient



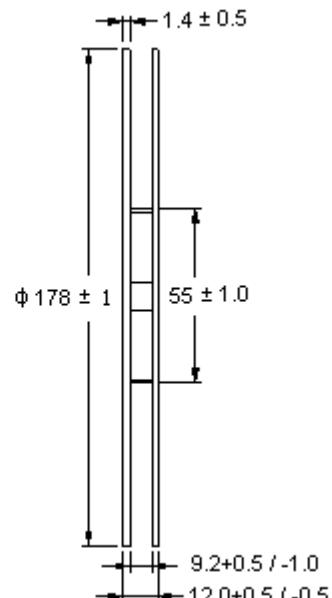
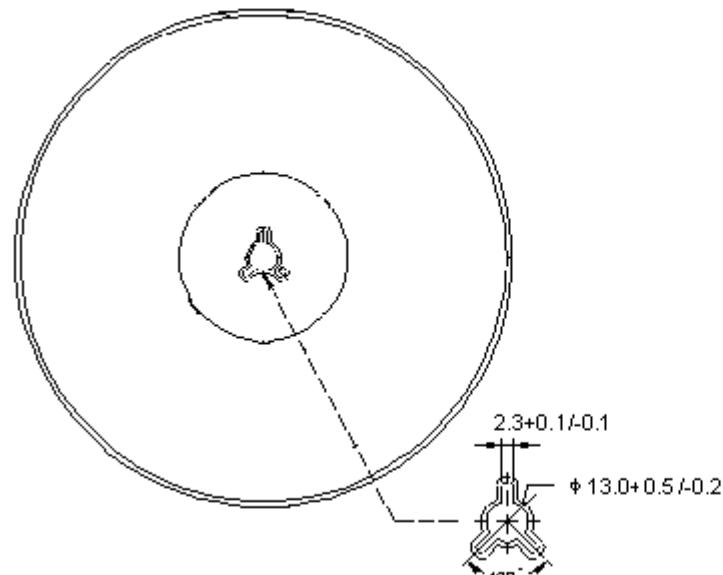
Transient Thermal Response Curves



## Recommended soldering footprint

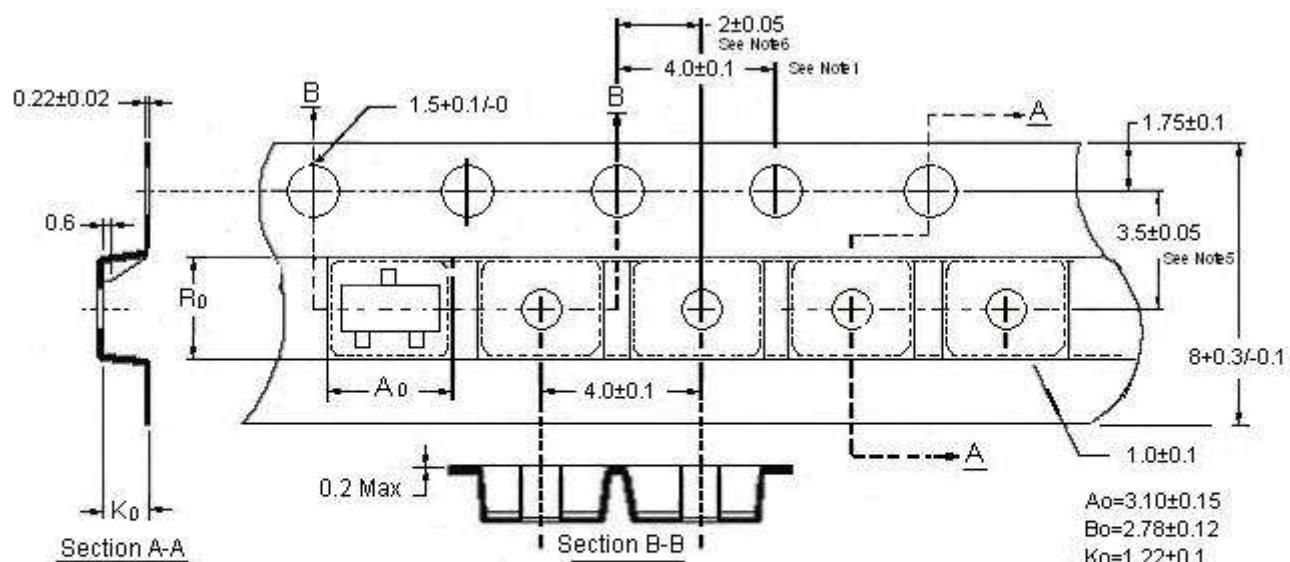


## Reel Dimension



Unit: millimeter

## Carrier Tape Dimension

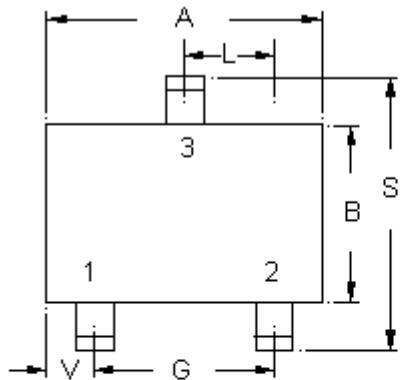


Notes:

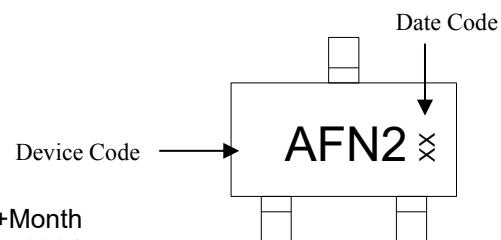
1. 10 sprocket hole pitch cumulative tolerance  $\pm 0.2$ .
2. Camber not to exceed 1mm in 100mm.
3. Material : conductive Black Polystyrene.
4.  $A_0$  &  $B_0$  measured on a plane 0.3mm above the bottom of the pocket.
5.  $K_0$  measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
6. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.

Unit : millimeter

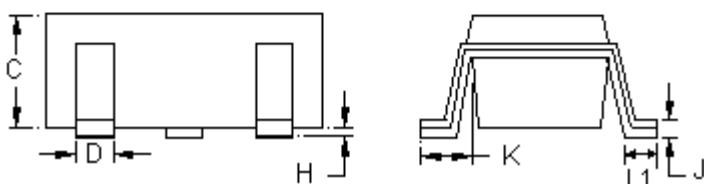
## SOT-23 Dimension



Marking:



Date Code: Year+Month  
 Year: 3→2003, 4→2004  
 Month: 1→1, 2→2, . . .  
 9→9, A→10, B→11, C→12



3-Lead SOT-23 Plastic Surface Mounted Package

Style: Pin 1.Gate 2.Source 3.Drain

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0032	0.0079	0.08	0.20
B	0.0472	0.0669	1.20	1.70	K	0.0118	0.0266	0.30	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1161	2.10	2.95
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0000	0.0040	0.00	0.10	L1	0.0118	0.0197	0.30	0.50